

L Number	Hits	Search Text	DB	Time stamp
229	189	((polymer or deposit or residue ) and ((plasma or gas\$2) near10 puls\$5) and semiconductor) ) and 438/\$.ccls.	USPAT; EPO; JPO; IBM_TDB	2002/10/24 13:11
230	875	((polymer or deposit or residue ) and ((plasma or gas\$2) near10 puls\$5) and semiconductor) ) and (contact or openings)	USPAT; EPO; JPO; IBM_TDB	2002/10/24 13:17
232	697	((polymer or deposit or residue ) and ((plasma or gas\$2) near10 puls\$5) and semiconductor) ) and (contact or openings)	USPAT; EPO; JPO; IBM_TDB	2002/10/24 15:32
235	19	(CHF3 or CF4 or CH2F2 or C4F8) same puls\$5	USPAT; EPO; JPO; IBM_TDB	2002/10/24 15:32
236	27	fluorocarbons same puls\$5 same (polymer or deposit)	USPAT; EPO; JPO; IBM_TDB	2002/10/24 15:28
237	21	(CHF3 or CF4 or CH2F2 or C4F8) and puls\$5 and (contact or openings or via) and polymer	USPAT; EPO; JPO; IBM_TDB	2002/10/24 15:18
240	121	fluorocarbons same puls\$5	USPAT; EPO; JPO; IBM_TDB	2002/10/24 15:28
241	108	(CHF3 or CF4 or CH2F2 or C4F8) and puls\$5 and (contact or openings or via)	USPAT; EPO; JPO; IBM_TDB	2002/10/24 16:04
242	321	(CHF3 or CF4 or CH2F2 or C4F8) and (contact or openings or via) and (polymer or residue or deposit)	USPAT; EPO; JPO; IBM_TDB	2002/10/24 16:07